Intel - EPF10K50EFI256-2 Datasheet





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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	360
Number of Logic Elements/Cells	2880
Total RAM Bits	40960
Number of I/O	191
Number of Gates	199000
Voltage - Supply	2.3V ~ 2.7V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	256-BGA
Supplier Device Package	256-FBGA (17x17)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k50efi256-2

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Functional Description

Each FLEX 10KE device contains an enhanced embedded array to implement memory and specialized logic functions, and a logic array to implement general logic.

The embedded array consists of a series of EABs. When implementing memory functions, each EAB provides 4,096 bits, which can be used to create RAM, ROM, dual-port RAM, or first-in first-out (FIFO) functions. When implementing logic, each EAB can contribute 100 to 600 gates towards complex logic functions, such as multipliers, microcontrollers, state machines, and DSP functions. EABs can be used independently, or multiple EABs can be combined to implement larger functions.

The logic array consists of logic array blocks (LABs). Each LAB contains eight LEs and a local interconnect. An LE consists of a four-input look-up table (LUT), a programmable flipflop, and dedicated signal paths for carry and cascade functions. The eight LEs can be used to create medium-sized blocks of logic—such as 8-bit counters, address decoders, or state machines—or combined across LABs to create larger logic blocks. Each LAB represents about 96 usable gates of logic.

Signal interconnections within FLEX 10KE devices (as well as to and from device pins) are provided by the FastTrack Interconnect routing structure, which is a series of fast, continuous row and column channels that run the entire length and width of the device.

Each I/O pin is fed by an I/O element (IOE) located at the end of each row and column of the FastTrack Interconnect routing structure. Each IOE contains a bidirectional I/O buffer and a flipflop that can be used as either an output or input register to feed input, output, or bidirectional signals. When used with a dedicated clock pin, these registers provide exceptional performance. As inputs, they provide setup times as low as 0.9 ns and hold times of 0 ns. As outputs, these registers provide clock-to-output times as low as 3.0 ns. IOEs provide a variety of features, such as JTAG BST support, slew-rate control, tri-state buffers, and open-drain outputs.

Embedded Array Block

The EAB is a flexible block of RAM, with registers on the input and output ports, that is used to implement common gate array megafunctions. Because it is large and flexible, the EAB is suitable for functions such as multipliers, vector scalars, and error correction circuits. These functions can be combined in applications such as digital filters and microcontrollers.

Logic functions are implemented by programming the EAB with a readonly pattern during configuration, thereby creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement any function with 8 inputs and 16 outputs. Parameterized functions such as LPM functions can take advantage of the EAB automatically.

The FLEX 10KE EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These small FPGA RAM blocks must be connected together to make RAM blocks of manageable size. The RAM blocks are connected together using multiplexers implemented with more logic blocks. These extra multiplexers cause extra delay, which slows down the RAM block. FPGA RAM blocks are also prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

The FLEX 10KE enhanced EAB adds dual-port capability to the existing EAB structure. The dual-port structure is ideal for FIFO buffers with one or two clocks. The FLEX 10KE EAB can also support up to 16-bit-wide RAM blocks and is backward-compatible with any design containing FLEX 10K EABs. The FLEX 10KE EAB can act in dual-port or single-port mode. When in dual-port mode, separate clocks may be used for EAB read and write sections, which allows the EAB to be written and read at different rates. It also has separate synchronous clock enable signals for the EAB read and write sections, which allow independent control of these sections.



Figure 4. FLEX 10KE Device in Single-Port RAM Mode

Note:

(1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 88 EAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 104 EAB local interconnect channels.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the write enable signal. In contrast, the EAB's synchronous RAM generates its own write enable signal and is self-timed with respect to the input or write clock. A circuit using the EAB's self-timed RAM must only meet the setup and hold time specifications of the global clock.

Figure 7. FLEX 10KE LAB



Notes:

- (1) EPF10K30E, EPF10K50E, and EPF10K50S devices have 22 inputs to the LAB local interconnect channel from the row; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 26.
- (2) EPF10K30E, EPF10K50E, and EPF10K50S devices have 30 LAB local interconnect channels; EPF10K100E, EPF10K130E, EPF10K200E, and EPF10K200S devices have 34.

LE Operating Modes

The FLEX 10KE LE can operate in the following four modes:

- Normal mode
- Arithmetic mode
- Up/down counter mode
- Clearable counter mode

Each of these modes uses LE resources differently. In each mode, seven available inputs to the LE—the four data inputs from the LAB local interconnect, the feedback from the programmable register, and the carry-in and cascade-in from the previous LE—are directed to different destinations to implement the desired logic function. Three inputs to the LE provide clock, clear, and preset control for the register. The Altera software, in conjunction with parameterized functions such as LPM and DesignWare functions, automatically chooses the appropriate mode for common functions such as counters, adders, and multipliers. If required, the designer can also create special-purpose functions that use a specific LE operating mode for optimal performance.

The architecture provides a synchronous clock enable to the register in all four modes. The Altera software can set DATA1 to enable the register synchronously, providing easy implementation of fully synchronous designs.

Clearable Counter Mode

The clearable counter mode is similar to the up/down counter mode, but supports a synchronous clear instead of the up/down control. The clear function is substituted for the cascade-in signal in the up/down counter mode. Use 2 three-input LUTs: one generates the counter data, and the other generates the fast carry bit. Synchronous loading is provided by a 2-to-1 multiplexer. The output of this multiplexer is AND ed with a synchronous clear signal.

Internal Tri-State Emulation

Internal tri-state emulation provides internal tri-states without the limitations of a physical tri-state bus. In a physical tri-state bus, the tri-state buffers' output enable (OE) signals select which signal drives the bus. However, if multiple OE signals are active, contending signals can be driven onto the bus. Conversely, if no OE signals are active, the bus will float. Internal tri-state emulation resolves contending tri-state buffers to a low value and floating buses to a high value, thereby eliminating these problems. The Altera software automatically implements tri-state bus functionality with a multiplexer.

Clear & Preset Logic Control

Logic for the programmable register's clear and preset functions is controlled by the DATA3, LABCTRL1, and LABCTRL2 inputs to the LE. The clear and preset control structure of the LE asynchronously loads signals into a register. Either LABCTRL1 or LABCTRL2 can control the asynchronous clear. Alternatively, the register can be set up so that LABCTRL1 implements an asynchronous load. The data to be loaded is driven to DATA3; when LABCTRL1 is asserted, DATA3 is loaded into the register.

During compilation, the Altera Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset



Figure 13. FLEX 10KE LAB Connections to Row & Column Interconnect

When dedicated inputs drive non-inverted and inverted peripheral clears, clock enables, and output enables, two signals on the peripheral control bus will be used.

Tables 8 and 9 list the sources for each peripheral control signal, and show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals. The tables also show the rows that can drive global signals.

Table 8. Peripheral Bus Sources for EPF10K30E, EPF10K50E & EPF10K50S Devices							
Peripheral Control Signal	EPF10K30E	EPF10K50E EPF10K50S					
OEO	Row A	Row A					
OE1	Row B	Row B					
OE2	Row C	Row D					
OE3	Row D	Row F					
OE4	Row E	Row H					
OE5	Row F	Row J					
CLKENA0/CLK0/GLOBAL0	Row A	Row A					
CLKENA1/OE6/GLOBAL1	Row B	Row C					
CLKENA2/CLR0	Row C	Row E					
CLKENA3/OE7/GLOBAL2	Row D	Row G					
CLKENA4/CLR1	Row E	Row I					
CLKENA5/CLK1/GLOBAL3	Row F	Row J					

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Table 20. 2.5-V EPF10K50E & EPF10K200E Device Recommended Operating Conditions								
Symbol	Parameter	Conditions	Min	Max	Unit			
V _{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	2.30 (2.30)	2.70 (2.70)	V			
V _{CCIO}	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V			
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.30 (2.30)	2.70 (2.70)	V			
VI	Input voltage	(5)	-0.5	5.75	V			
Vo	Output voltage		0	V _{CCIO}	V			
Τ _A	Ambient temperature	For commercial use	0	70	°C			
		For industrial use	-40	85	°C			
TJ	Operating temperature	For commercial use	0	85	°C			
		For industrial use	-40	100	°C			
t _R	Input rise time			40	ns			
t _F	Input fall time			40	ns			

Table 21. 2.5-V EPF10K30E, EPF10K50S, EPF10K100E, EPF10K130E & EPF10K200S Device Recommended Operating Conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CCINT}	Supply voltage for internal logic and input buffers	(3), (4)	2.375 (2.375)	2.625 (2.625)	V
V _{CCIO}	Supply voltage for output buffers, 3.3-V operation	(3), (4)	3.00 (3.00)	3.60 (3.60)	V
	Supply voltage for output buffers, 2.5-V operation	(3), (4)	2.375 (2.375)	2.625 (2.625)	V
VI	Input voltage	(5)	-0.5	5.75	V
Vo	Output voltage		0	V _{CCIO}	V
Τ _A	Ambient temperature	For commercial use	0	70	°C
		For industrial use	-40	85	°C
Τ _J	Operating temperature	For commercial use	0	85	°C
		For industrial use	-40	100	°C
t _R	Input rise time			40	ns
t _F	Input fall time			40	ns

Timing simulation and delay prediction are available with the Altera Simulator and Timing Analyzer, or with industry-standard EDA tools. The Simulator offers both pre-synthesis functional simulation to evaluate logic design accuracy and post-synthesis timing simulation with 0.1-ns resolution. The Timing Analyzer provides point-to-point timing delay information, setup and hold time analysis, and device-wide performance analysis.

Figure 24 shows the overall timing model, which maps the possible paths to and from the various elements of the FLEX 10KE device.



Figures 25 through 28 show the delays that correspond to various paths and functions within the LE, IOE, EAB, and bidirectional timing models.

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Table 24. LE Timing Microparameters (Part 2 of 2) Note (1)					
Symbol	Parameter	Condition			
t _{CLR}	LE register clear delay				
t _{CH}	Minimum clock high time from clock pin				
t _{CL}	Minimum clock low time from clock pin				

Table 25. IOE	Timing Microparameters Note (1)	
Symbol	Parameter	Conditions
t _{IOD}	IOE data delay	
t _{IOC}	IOE register control signal delay	
t _{IOCO}	IOE register clock-to-output delay	
t _{IOCOMB}	IOE combinatorial delay	
t _{IOSU}	IOE register setup time for data and enable signals before clock; IOE register recovery time after asynchronous clear	
t _{IOH}	IOE register hold time for data and enable signals after clock	
t _{IOCLR}	IOE register clear time	
t _{OD1}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF (2)
t _{OD2}	Output buffer and pad delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF (3)
t _{OD3}	Output buffer and pad delay, slow slew rate = on	C1 = 35 pF (4)
t _{XZ}	IOE output buffer disable delay	
t _{ZX1}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 3.3 V	C1 = 35 pF (2)
t _{ZX2}	IOE output buffer enable delay, slow slew rate = off, V_{CCIO} = 2.5 V	C1 = 35 pF (3)
t _{ZX3}	IOE output buffer enable delay, slow slew rate = on	C1 = 35 pF (4)
t _{INREG}	IOE input pad and buffer to IOE register delay	
t _{IOFD}	IOE register feedback delay	
t _{INCOMB}	IOE input pad and buffer to FastTrack Interconnect delay	

Figures 29 and 30 show the asynchronous and synchronous timing waveforms, respectively, or the EAB macroparameters in Tables 26 and 27.

EAB Asynchronous Read WE _ a0 a2 Address a1 a3 – t_{EABAA}t_{EABRCCOMB} Data-Out d0 d3 d1 d2 **EAB Asynchronous Write** WE t_{EABWP} ► t_{EABWDH} t_{EABWDSU} Þ. din0 din1 Data-In t_{EABWASU} t_{EABWAH} t_{EABWCCOMB} Address a0 a1 a2 t_{EABDD} Data-Out din0 din1 dout2

Figure 29. EAB Asynchronous Timing Waveforms

Figure 30. EAB Synchronous Timing Waveforms



EAB Synchronous Write (EAB Output Registers Used)



Tables 31 through 37 show EPF10K30E device internal and external timing parameters.

Table 31. EPF10K30E Device LE Timing Microparameters (Part 1 of 2) Note (1)								
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit	
	Min	Max	Min	Max	Min	Max		
t _{LUT}		0.7		0.8		1.1	ns	
t _{CLUT}		0.5		0.6		0.8	ns	
t _{RLUT}		0.6		0.7		1.0	ns	
t _{PACKED}		0.3		0.4		0.5	ns	
t _{EN}		0.6		0.8		1.0	ns	
t _{CICO}		0.1		0.1		0.2	ns	
t _{CGEN}		0.4		0.5		0.7	ns	

Table 31. EPF10K30E Device LE Timing Microparameters (Part 2 of 2) Note (1)							
Symbol	-1 Spee	d Grade	-2 Spee	d Grade	-3 Spee	ed Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{CGENR}		0.1		0.1		0.2	ns
t _{CASC}		0.6		0.8		1.0	ns
t _C		0.0		0.0		0.0	ns
t _{CO}		0.3		0.4		0.5	ns
t _{COMB}		0.4		0.4		0.6	ns
t _{SU}	0.4		0.6		0.6		ns
t _H	0.7		1.0		1.3		ns
t _{PRE}		0.8		0.9		1.2	ns
t _{CLR}		0.8		0.9		1.2	ns
t _{CH}	2.0		2.5		2.5		ns
t _{CL}	2.0		2.5		2.5		ns

Table 32. EPF10K30E Device IOE Timing Microparameters Note (1)							
Symbol	-1 Spee	ed Grade	-2 Spee	ed Grade	-3 Spee	ed Grade	Unit
	Min	Max	Min	Max	Min	Мах	
t _{IOD}		2.4		2.8		3.8	ns
t _{IOC}		0.3		0.4		0.5	ns
t _{IOCO}		1.0		1.1		1.6	ns
t _{IOCOMB}		0.0		0.0		0.0	ns
t _{IOSU}	1.2		1.4		1.9		ns
t _{IOH}	0.3		0.4		0.5		ns
t _{IOCLR}		1.0		1.1		1.6	ns
t _{OD1}		1.9		2.3		3.0	ns
t _{OD2}		1.4		1.8		2.5	ns
t _{OD3}		4.4		5.2		7.0	ns
t _{XZ}		2.7		3.1		4.3	ns
t _{ZX1}		2.7		3.1		4.3	ns
t _{ZX2}		2.2		2.6		3.8	ns
t _{ZX3}		5.2		6.0		8.3	ns
t _{INREG}		3.4		4.1		5.5	ns
t _{IOFD}		0.8		1.3		2.4	ns
t _{INCOMB}		0.8		1.3		2.4	ns

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Table 34. EPF10K30E Device EAB Internal Timing Macroparameters Note (1)							
Symbol	-1 Spee	ed Grade	-2 Spee	ed Grade	-3 Spee	ed Grade	Unit
	Min	Max	Min	Max	Min	Мах	
t _{EABAA}		6.4		7.6		8.8	ns
t _{EABRCOMB}	6.4		7.6		8.8		ns
t _{EABRCREG}	4.4		5.1		6.0		ns
t _{EABWP}	2.5		2.9		3.3		ns
t _{EABWCOMB}	6.0		7.0		8.0		ns
t _{EABWCREG}	6.8		7.8		9.0		ns
t _{EABDD}		5.7		6.7		7.7	ns
t _{EABDATACO}		0.8		0.9		1.1	ns
t _{EABDATASU}	1.5		1.7		2.0		ns
t _{EABDATAH}	0.0		0.0		0.0		ns
t _{EABWESU}	1.3		1.4		1.7		ns
t _{EABWEH}	0.0		0.0		0.0		ns
t _{EABWDSU}	1.5		1.7		2.0		ns
t _{EABWDH}	0.0		0.0		0.0		ns
t _{EABWASU}	3.0		3.6		4.3		ns
t _{EABWAH}	0.5		0.5		0.4		ns
t _{EABWO}		5.1		6.0		6.8	ns

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Table 41. EPF10K50E Device EAB Internal Timing Macroparameters Note (1)							
Symbol	-1 Spee	d Grade	-2 Spee	ed Grade	-3 Spee	d Grade	Unit
	Min	Max	Min	Max	Min	Max	
t _{EABAA}		6.4		7.6		10.2	ns
t _{EABRCOMB}	6.4		7.6		10.2		ns
t _{EABRCREG}	4.4		5.1		7.0		ns
t _{EABWP}	2.5		2.9		3.9		ns
t _{EABWCOMB}	6.0		7.0		9.5		ns
t _{EABWCREG}	6.8		7.8		10.6		ns
t _{EABDD}		5.7		6.7		9.0	ns
t _{EABDATACO}		0.8		0.9		1.3	ns
t _{EABDATASU}	1.5		1.7		2.3		ns
t _{EABDATAH}	0.0		0.0		0.0		ns
t _{EABWESU}	1.3		1.4		2.0		ns
t _{EABWEH}	0.0		0.0		0.0		ns
t _{EABWDSU}	1.5		1.7		2.3		ns
t _{EABWDH}	0.0		0.0		0.0		ns
t _{EABWASU}	3.0		3.6		4.8		ns
t _{EABWAH}	0.5		0.5		0.8		ns
t _{EABWO}		5.1		6.0		8.1	ns

Table 42. EPF10K50E Device Interconnect Timing Microparameters Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{DIN2IOE}		3.5		4.3		5.6	ns
t _{DIN2LE}		2.1		2.5		3.4	ns
t _{DIN2DATA}		2.2		2.4		3.1	ns
t _{DCLK2IOE}		2.9		3.5		4.7	ns
t _{DCLK2LE}		2.1		2.5		3.4	ns
t _{SAMELAB}		0.1		0.1		0.2	ns
t _{SAMEROW}		1.1		1.1		1.5	ns
t _{SAMECOLUMN}		0.8		1.0		1.3	ns
t _{DIFFROW}		1.9		2.1		2.8	ns
t _{TWOROWS}		3.0		3.2		4.3	ns
t _{LEPERIPH}		3.1		3.3		3.7	ns
t _{LABCARRY}		0.1		0.1		0.2	ns
t _{LABCASC}		0.3		0.3		0.5	ns

Table 48. EPF10K100E Device EAB Internal Timing Macroparameters (Part 2 of 2) Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{EABWCOMB}	5.9		7.7		10.3		ns
t _{EABWCREG}	5.4		7.0		9.4		ns
t _{EABDD}		3.4		4.5		5.9	ns
t _{EABDATACO}		0.5		0.7		0.8	ns
t _{EABDATASU}	0.8		1.0		1.4		ns
t _{EABDATAH}	0.1		0.1		0.2		ns
t _{EABWESU}	1.1		1.4		1.9		ns
t _{EABWEH}	0.0		0.0		0.0		ns
t _{EABWDSU}	1.0		1.3		1.7		ns
t _{EABWDH}	0.2		0.2		0.3		ns
t _{EABWASU}	4.1		5.2		6.8		ns
t _{EABWAH}	0.0		0.0		0.0		ns
t _{EABWO}		3.4		4.5		5.9	ns

 Table 49. EPF10K100E Device Interconnect Timing Microparameters
 Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{DIN2IOE}		3.1		3.6		4.4	ns
t _{DIN2LE}		0.3		0.4		0.5	ns
t _{DIN2DATA}		1.6		1.8		2.0	ns
t _{DCLK2IOE}		0.8		1.1		1.4	ns
t _{DCLK2LE}		0.3		0.4		0.5	ns
t _{SAMELAB}		0.1		0.1		0.2	ns
t _{SAMEROW}		1.5		2.5		3.4	ns
t _{SAMECOLUMN}		0.4		1.0		1.6	ns
t _{DIFFROW}		1.9		3.5		5.0	ns
t _{TWOROWS}		3.4		6.0		8.4	ns
t _{LEPERIPH}		4.3		5.4		6.5	ns
t _{LABCARRY}		0.5		0.7		0.9	ns
t _{LABCASC}		0.8		1.0		1.4	ns

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Table 59. EPF10K200E Device LE Timing Microparameters (Part 2 of 2) Note (1)							
Symbol	-1 Spee	d Grade -2 Speed G		d Grade	I Grade -3 Speed Grade		Unit
	Min	Мах	Min	Max	Min	Max	
t _H	0.9		1.1		1.5		ns
t _{PRE}		0.5		0.6		0.8	ns
t _{CLR}		0.5		0.6		0.8	ns
t _{CH}	2.0		2.5		3.0		ns
t _{CL}	2.0		2.5		3.0		ns

Table 60. EPF10K200E Device IOE Timing Microparameters Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t _{IOD}		1.6		1.9		2.6	ns
t _{IOC}		0.3		0.3		0.5	ns
t _{IOCO}		1.6		1.9		2.6	ns
t _{IOCOMB}		0.5		0.6		0.8	ns
t _{IOSU}	0.8		0.9		1.2		ns
t _{IOH}	0.7		0.8		1.1		ns
t _{IOCLR}		0.2		0.2		0.3	ns
t _{OD1}		0.6		0.7		0.9	ns
t _{OD2}		0.1		0.2		0.7	ns
t _{OD3}		2.5		3.0		3.9	ns
t _{XZ}		4.4		5.3		7.1	ns
t _{ZX1}		4.4		5.3		7.1	ns
t _{ZX2}		3.9		4.8		6.9	ns
t _{ZX3}		6.3		7.6		10.1	ns
t _{INREG}		4.8		5.7		7.7	ns
t _{IOFD}		1.5		1.8		2.4	ns
t _{INCOMB}		1.5		1.8		2.4	ns

Table 69. EPF10K50S Device EAB Internal Timing Macroparameters Note (1)							
Symbol	-1 Spee	-1 Speed Grade		-2 Speed Grade		ed Grade	Unit
	Min	Max	Min	Мах	Min	Max	
t _{EABAA}		3.7		5.2		7.0	ns
t _{EABRCCOMB}	3.7		5.2		7.0		ns
t _{EABRCREG}	3.5		4.9		6.6		ns
t _{EABWP}	2.0		2.8		3.8		ns
t _{EABWCCOMB}	4.5		6.3		8.6		ns
t _{EABWCREG}	5.6		7.8		10.6		ns
t _{EABDD}		3.8		5.3		7.2	ns
t _{EABDATACO}		0.8		1.1		1.5	ns
t _{EABDATASU}	1.1		1.6		2.1		ns
t _{EABDATAH}	0.0		0.0		0.0		ns
t _{EABWESU}	0.7		1.0		1.3		ns
t _{EABWEH}	0.4		0.6		0.8		ns
t _{EABWDSU}	1.2		1.7		2.2		ns
t _{EABWDH}	0.0		0.0		0.0		ns
t _{EABWASU}	1.6		2.3		3.0		ns
t _{EABWAH}	0.9		1.2		1.8		ns
t _{EABWO}		3.1		4.3		5.9	ns

Table 70. EPF10K50S Device Interconnect Timing Microparameters Note (1)							
Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Мах	
t _{DIN2IOE}		3.1		3.7		4.6	ns
t _{DIN2LE}		1.7		2.1		2.7	ns
t _{DIN2DATA}		2.7		3.1		5.1	ns
t _{DCLK2IOE}		1.6		1.9		2.6	ns
t _{DCLK2LE}		1.7		2.1		2.7	ns
t _{SAMELAB}		0.1		0.1		0.2	ns
t _{SAMEROW}		1.5		1.7		2.4	ns
t _{SAMECOLUMN}		1.0		1.3		2.1	ns
t _{DIFFROW}		2.5		3.0		4.5	ns
t _{TWOROWS}		4.0		4.7		6.9	ns
t _{LEPERIPH}		2.6		2.9		3.4	ns
t _{LABCARRY}		0.1		0.2		0.2	ns
t _{LABCASC}		0.8		1.0		1.3	ns

Power Consumption	The supply power (P) for FLEX 10KE devices can be calculated with the following equation:						
	$P = P_{INT} + P_{IO} = (I_{CCSTANDBY} + I_{CCACTIVE}) \times V_{CC} + P_{IO}$						
	The $I_{CCACTIVE}$ value depends on the switching frequency and the application logic. This value is calculated based on the amount of current that each LE typically consumes. The P_{IO} value, which depends on the device output load characteristics and switching frequency, can be calculated using the guidelines given in <i>Application Note 74 (Evaluating Power for Altera Devices)</i> .						
	Compared to the rest of the device, the embedded array consumes a negligible amount of power. Therefore, the embedded array can be ignored when calculating supply current.						
	The $I_{CCACTIVE}$ value can be calculated with the following equation:						
	$I_{CCACTIVE} = K \times f_{MAX} \times N \times tog_{LC} \times \frac{\mu A}{MHz \times LE}$						
	Where:						
	Table of provides the constant (K) values for FLEA TUKE devices.						
	Table 80. FLEX 10KE K Constant Values						
	Device	K Value					
	EPF10K30E	4.5					
	EPF10K50E	4.8					
	EPF10K50S	4.5					
	EPF10K100E	4.5					
	EPF10K130E	4.6					
	EPF10K200E	4.8					

EPF10K200S

This calculation provides an I_{CC} estimate based on typical conditions with no output load. The actual I_{CC} should be verified during operation because this measurement is sensitive to the actual pattern in the device and the environmental operating conditions.

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